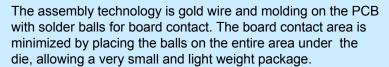
# FD-FBGA

### **Face Down-Fine pitch BGA**

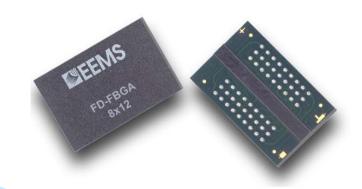
EEMS offers the FD-FBGA as a near Chip Size Package, based on a BT laminate substrate with a Ball Grid Array format.

The FD-FBGA has been developped to accommodate devices with pads in the center of the die, like most of the DRAM are. Such specific geometry requires the active side of the die to face down on the substrate.



Body sizes and ball counts are designed to fit the specific customers needs (the two Tables show the range of the FD-FBGA capabilities and the already tooled packages).

These packages are also well suited to products requiring low inductance as the PCB design can take this requirement into account and be designed accordingly.



#### Features & Benefits

- Small board area needed
- Small size
- Cost competitive
- High reliability
- Compliant to Rohs directive 2002/95/CE
- Die Stack capability

# **Applications**

High Speed Memory (Sdram, DDR, DDRII) and anywhere a Center Bond Device requires a smaller footprint, a FD-FBGA should be used.

#### Device End Equipment

SDRAM

DRAM

DDR

All Center Bond Memory

Portable PC's

Desktop PC's

Wireless Applications

Mobile phones

PDA's

FD-FBGA Capabilities								
Item Min.		Max.	Notes					
Foot Print (mm)	5 x 5	17 x 17	All dimensions in increment of 0.1 mm, quad and rectangular					
Thickness (mm)	1.00	1.70	All dimensions in increment of 0.1 mm					
Ball Dia (um)	300	500	All dimensions in increment of 50 um					
Ball Arrays	5 x 5	21 x 21	Full matrix and depopulated					
Ball Pitches (mm)	0.5	1.0	0.65, 0.75, 0.80 mm also available					

### Standard Materials

Substrate BT or equivalent Die Attach Low stress Tape Gold wire 24 - 30 um

Mold Compound Epoxy

Eutectic 63/37 or Solder Ball

Sn/4.0Ag/0.5Cu alloy Jedec Tray/Tape & Reel

Packing option Dry Pack

### **Process Highlights**

Processable wafer 200 - 300 mm Die Tickness 0.240 mm max Bond Pad Pitch 50 um min Marking Laser

Ball inspection Auto inspection



Packing

# FD-FBGA

# **Specifications**

### Electrical (simulated w/bondwire)

(8 x 12 mm body with 60 balls)

Capacitance (pF) : 0.32 - 0.55 at 1.5 GHz Inductance (nH) : 1.8 - 3.0 at 1.5 GHz Resistance (m $\Omega$ ) : 280 - 420 at 1.5 Ghz

### Thermal Resistance (simulated)

(8 x 12 mm body with 60 balls; single layer PCB and 1 Watt, 0 m/s airflow as per JEDEC JESD51.2):

Θ ja = 32 °C/watt Typical

# Reliability

Moisture Sensitivity : JEDEC MSL 3 @ up to 260 °C,

High Temp Storage : 150 °C, 1000 hours

Temp Cycle : -55/+125 °C, 1000 cicles

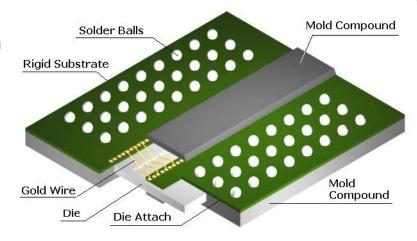
UHAST : 130 °C /85% RH, 240 hours

T & H : 85 °C/85% RH, 1000 hours

### **Available Services**

- PCB Design and simulation
- 300 mm wafer full processing
- Wafer backgrinding
- Wafer map / sort
- Product Engineering
- -30 + 125 °C full test
- · Dynamic Burn In
- Compliant to Rohs directive 2002/95/CE

## Cross - Section



FD-FBGA Tooled Packages: Nominal Dimensions (mm)											
ID Letter	Body Size	Ball Count	Ball Pitch	Ball Matrix	Ball Diameter	PCB Thickness	Mold Cap Thickness	Total Thickness			
T-FBGA	8 x 12	54	0.80	9 x 9	0.40	0.29	0.56	1.2 max			
T-FBGA	8 x 12	60	0.80 x 1.0	6 x 12	0.40	0.29	0.56	1.2 max			
T-FBGA	8 x 12	60	0.80 x 1.0	6 x 12	0.45	0.29	0.56	1.2 max			
T-FBGA	10 x 10.5	60	0.80	6 x 12	0.45	0.29	0.56	1.2 max			
T-FBGA	10 x 12.5	84	0.80	6 x 15	0.45	0.29	0.56	1.2 max			

